

2SC2236 TRANSISTOR(NPN)

FEATURES

Power dissipation

P_{CM} : 0.9W ($T_{amb}=25^{\circ}C$)

Collector current

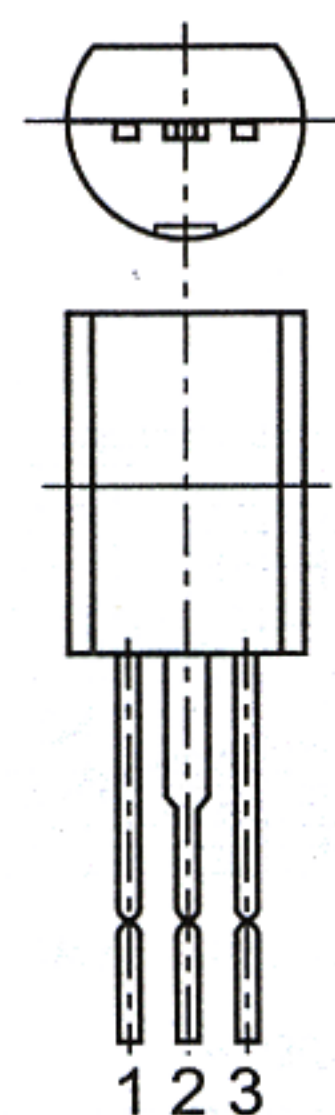
I_{CM} : 1.5 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



TO-92MOD

1.EMITTER

2.COLLECTOR

3.BASE

1 2 3

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 1 \text{ mA}, I_E = 0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 1 \text{ mA}, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30 \text{ V}, I_E = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 2 \text{ V}, I_C = 500 \text{ mA}$	100	320	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 1.5 \text{ A}, I_B = 0.03 \text{ A}$		2	V
Base-emitter voltage	V_{BE}	$I_C = 500 \text{ mA}, V_{CE} = 2 \text{ V}$		1	V
Transition frequency	f_T	$V_{CE} = 2 \text{ V}, I_C = 500 \text{ mA}$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

